

12/12/2005

PRODUCT RELIABILITY REPORT FOR

DS1388, Rev A2

# **Dallas Semiconductor**

4401 South Beltwood Parkway Dallas, TX 75244-3292

Prepared by:

Don Lipps Staff Reliability Engineer Dallas Semiconductor 4401 South Beltwood Pkwy. Dallas, TX 75244-3292 Email : don.lipps@dalsemi.com ph: 972-371-3739 fax: 972-371-6016

## Conclusion

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products:

#### DS1388, Rev A2

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

## **Device Description:**

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l\_datasheet3.cfm.

## **Reliability Derating:**

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)\*(1/Tu - 1/Ts)) = tu/ts AfT = Acceleration factor due to Temperature tu = Time at use temperature (e.g. 55°C) ts = Time at stress temperature (e.g. 125°C) k = Boltzmann's Constant (8.617 x 10-5 eV/°K) Tu = Temperature at Use (°K) Ts = Temperature at Stress (°K) Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B\*(Vs - Vu)) AfV = Acceleration factor due to Voltage Vs = Stress Voltage (e.g. 7.0 volts) Vu = Maximum Operating Voltage (e.g. 5.5 volts) B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts \* AfV \* AfT \* N \* 2)X = Chi-Sq statistical upper limit N = Life test sample size Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5	Volt
--	------

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "\*" after DATE CODE denotes specific product

#### **Device Information:**

Process:	E35WN-3P3M,DPE2,NTC,DSD,PDESD,PDRES,Cap,ENPN
Passivation:	TEOS Ox-Nit 2-Mask Laser/Pass for E35WM; Full BEOL at
Die Size:	78 x 79
Number of Transistors:	23551
Interconnect:	Aluminum / 1% Silicon / 0.5% Copper
Gate Oxide Thickness:	120 Å

#### ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE COD	CONDITION	REA	DPOINT	QTY	FAILS	FA#
ESD SENSITIVITY	0541 *	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0541 *	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0541 *	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0541 *	EOS/ESD S5.1 HBM 3000 VOLTS	1	PUL'S	3	1	No FA
ESD SENSITIVITY	0541 *	EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	1	No FA
LATCH-UP	0541 *	JESD78, I-TEST 125C	2	DYS	6	0	
LATCH-UP	0541 *	JESD78, Vsupply TEST 125C	2	DYS	6	0	
				Total:		2	

OPERATING LIFE

DESCRIPTION	DATE COD	CONDITION	READPOINT	QTY FA	ILS	FA#
HIGH TEMP OP LIFE	0451	125C, 5.25 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0512	125C, 5.25 VOLTS	1000 HRS	77	0	
HIGH TEMP REVERSE BIAS	0530	125C, 5.25 VOLTS	1000 HRS	80	0	
HIGH TEMP REVERSE BIAS	0530	125C, 5.25 VOLTS	1000 HRS	80	0	
HIGH TEMP REVERSE BIAS	0530	125C, 5.25 VOLTS	1000 HRS	80	0	

HIGH TEMP OP LIFE	0533	125C, 5.25 VOLTS		1000	HRS	77	0	
HIGH TEMP OP LIFE	0541 *	125C, 5.5 VOLTS		192	HRS	77	0	
HIGH TEMP OP LIFE	0547	125C, 5.25 VOLTS		192	HRS	77	0	
					Fotal:		0	
W/E ENDURANCE AN	D DATA RET	'N						
DESCRIPTION	DATE COD	CONDITION		READ	POINT	QTY	FAILS	FA#
WRITE CYCLE STRESS (KCYS)	0451	85 C, 5.25 VOLTS		50	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0451	25 C, 5.25 VOLTS		200	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0512	25 C, 5.25 VOLTS		200	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0533	85 C, 5.25 VOLTS		50	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	1 3	30041503
WRITE CYCLE STRESS (KCYS)	0533	25 C, 5.25 VOLTS		200	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0533	85 C, 5.25 VOLTS		50	KCYS	77	0	
STORAGE LIFE		175C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0535	85 C, 5.25 VOLTS		50	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0535	25 C, 5.25 VOLTS		200	KCYS	77	0	
STORAGE LIFE		150C		1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0541 *	85 C, 5.5 VOLTS		50	KCYS	77	0	
STORAGE LIFE	*	150C		120	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0547	85 C, 5.25 VOLTS		50	KCYS	77	0	
			Total: 1					
FAILURE RATE:	MT	TF (YRS): 58819	FITS:	1.9				

30041503 - Failure analysis in process.